

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	537	chip\$1on\$1chip	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 11:21
L3	56	(Kazutaka Shibata).in. and chip\$1on\$1chip	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 11:38
L2	69	chip\$1on\$1chip same IC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 11:38
L4	46	(Kazutaka near2 Shibata).in. and chip\$1on\$1chip	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 11:40
L5	3	"200115223"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 11:45
L6	7	"1154474"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 11:55
L7	306	(warp\$ or bow\$5) same resin same (grind\$5 or polish\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 11:56
L8	88	(warp\$ or bow\$5) same resin same (grind\$5 or polish\$5) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 14:18
L10	2	"6455920".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 14:23

L9	1	"6495914".pn. and cut\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 14:23
S19	10	semiconductor near3 chip near10 active same resin same (polish\$ or grind\$)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:23
L13	366	semiconductor near3 chip same resin same (polish\$ or grind\$)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:23
S34	44	resin near10 (polish\$4 or grind\$) near10 thick\$ same (back or back\$1side or rear) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:24
S29	46	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) near20 expos\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:24
S16	30	semiconductor near3 chip same resin same electrode same (polish\$ or grind\$) same (rear or back)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:24
S15	68	semiconductor near3 chip and resin same electrode same (polish\$ or grind\$) same (rear or back)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:24
L17	386	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:24
L16	89	semiconductor near3 chip and resin same electrode same (polish\$ or grind\$) same (rear or back)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:24
L15	34	semiconductor near3 chip same resin same electrode same (polish\$ or grind\$) same (rear or back)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:24

L14	56	resin near10 (polish\$4 or grind\$) near10 thick\$ same (back or back\$1side or rear) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:24
S9	120	resin near10 (back or back\$1sid\$) near10 (polish\$ or grind\$) and semiconduct\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:25
L19	158	resin near10 (back or back\$1sid\$) near10 (polish\$ or grind\$) and semiconduct\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:25
L18	29	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) near20 electroduct\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 15:25